SFT1341

Power MOSFET

–40V, 112m Ω , –10A, Single P-Channel

ON Semiconductor®

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Features

- Low On-Resistance
- Low Gate Charge
- ESD Diode-Protected Gate
- High Speed Switching
- Low Gate Drive Voltage
- Pb-free and RoHS Compliance

Specifications

Absolute Maximum Ratings at Ta = 25°C

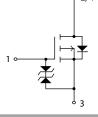
Parameter		Symbol	Value	Unit
Drain to Source Voltage		V _{DSS}	-40	V
Gate to Source Voltage		VGSS	±10	٧
Drain Current (DC)		ID	-10	Α
Drain Current PW≤10μs, duty cycle≤1%		IDP	-40	А
Power Dissipation			1.0	W
	Tc=25°C	PD	15	W
Junction Temperature		Tj	150	°C
Storage Temperature		Tstg	-55 to +150	°C

Thermal Resistance Ratings

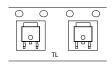
Parameter	Symbol	Value	Unit	
Junction to Case Steady State	$R_{\theta JC}$	8.33	0000	
Junction to Ambient *1	$R_{\theta JA}$	125	°C/W	

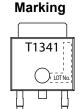
Note: *1 Insertion mounted

P-Channel



Packing Type:TL









Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

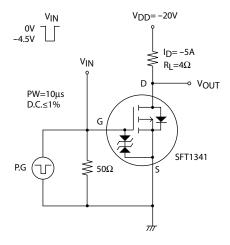
SFT1341

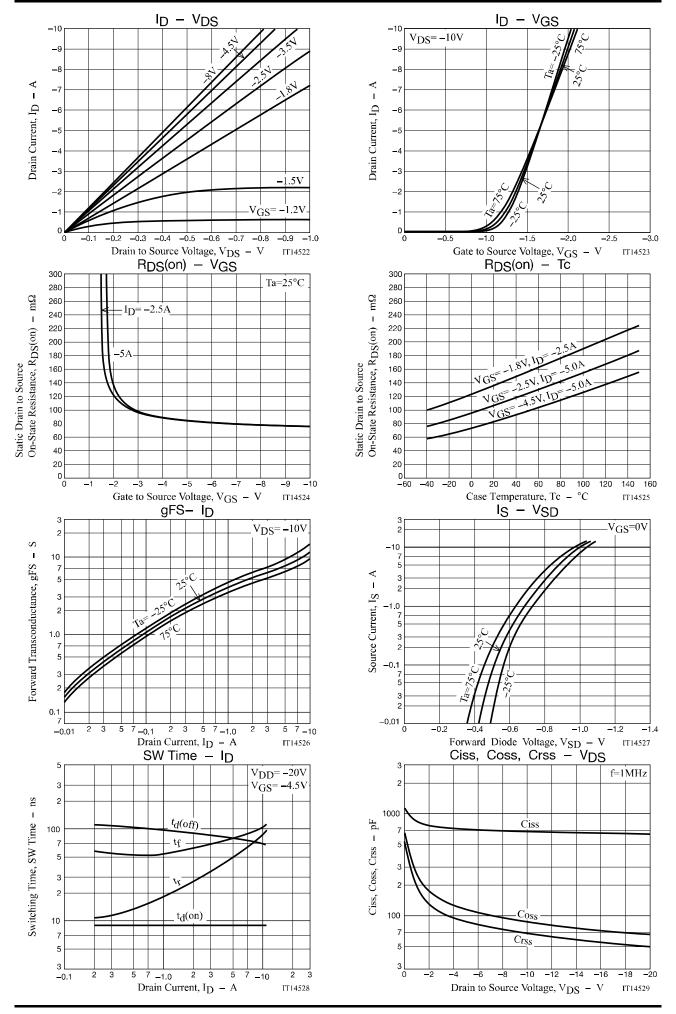
Electrical Characteristics at Ta = 25°C

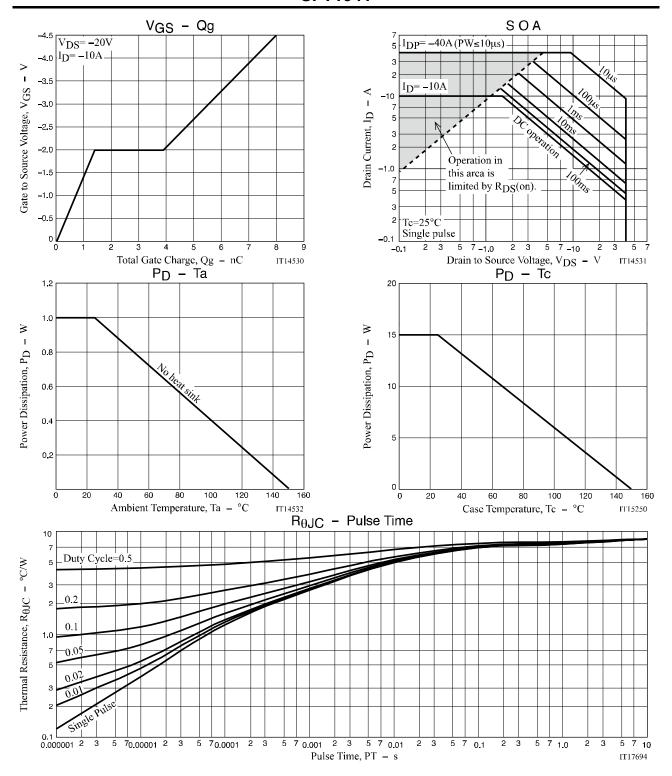
Parameter	O. made al	Q a livi		Value			
Parameter	Symbol	mbol Conditions		typ	max	Unit	
Drain to Source Breakdown Voltage	V(BR)DSS	I _D = -1mA, V _{GS} =0V	-40			٧	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} = -40V, V _{GS} =0V			-1	μΑ	
Gate to Source Leakage Current	IGSS	VGS=±8V, VDS=0V			±10	μΑ	
Gate Threshold Voltage	V _{GS} (th)	V _{DS} = -10V, I _D = -1mA	-0.4		-1.4	V	
Forward Transconductance	9FS	V _{DS} = -10V, I _D = -5A	4.6	7.7		S	
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D = -5A, V _G S= -4.5V		86	112	mΩ	
	R _{DS} (on)2	I _D = -5A, V _G S= -2.5V		110	154	mΩ	
	R _{DS} (on)3	I _D = -2.5A, V _G S= -1.8V		140	210	mΩ	
Input Capacitance	Ciss			650		pF	
Output Capacitance	Coss	V _{DS} = -20V, f=1MHz		65		pF	
Reverse Transfer Capacitance	Crss			50		pF	
Turn-ON Delay Time	t _d (on)			9.0		ns	
Rise Time	t _r]		50		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		81		ns	
Fall Time	tf	1		80		ns	
Total Gate Charge	Qg			8.0		nC	
Gate to Source Charge	Qgs	V _{DS} = -20V, V _{GS} = -4.5V, I _D = -10A		1.4		nC	
Gate to Drain "Miller" Charge	Qgd	1		2.5		nC	
Forward Diode Voltage	V _{SD}	I _S = -10A, V _{GS} =0V		-1.0	-1.5	V	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit







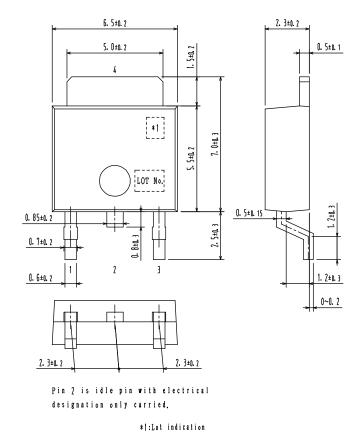
Package Dimensions SFT1341-TL-E/SFT1341-TL-W

DPAK/TP-FA

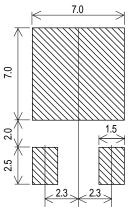
unit: mm



- 1:Gate
- 2:Drain
- 3:Source
- 4:Drain



Recommended **Soldering Footprint**



Package Dimensions

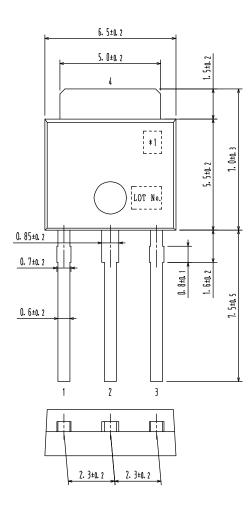
SFT1341-E/SFT1341-W

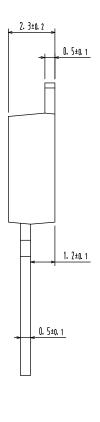
IPAK/TP

Unit: mm



- 1:Gate
- 2:Drain
- 3:Source
- 4:Drain





*1:Lot indication

Ordering & Package Information

Device	Package	Shipping	Note
SFT1341-E	IPAK(TP)		Pb-Free
SFT1341-W	SC-64 TO-251	500pcs. / bag	Pb-Free and Halogen Free
SFT1341-TL-E	DPAK(TP-FA)		Pb-Free
SFT1341-TL-W	SC-63 700pcs. / reel TO-252	Pb-Free and Halogen Free	

Note on usage: Since the SFT1341 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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